

DMN3150L N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

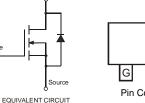
- Low On-Resistance: $R_{DS(ON)} < 85m\Omega @ V_{GS} = 4.5V, I_D = 3.6A$ $R_{DS(ON)} < 115m\Omega @ V_{GS} = 2.5V, I_D = 3.1A$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

Drai

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)





Pin Configuration

S

D

Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V _{DSS}	28	V
Gate-Source Voltage		V _{GSS}	±12	V
Drain Current (Note 1)	T _A = 25°C T _A = 70°C	ID	3.2 2.8	А
Drain Current (Note 1)	Pulsed	I _{DM}	10	A
Body-Diode Continuous Current (Note 1)		Is	2.0	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	PD	1.25	W
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 1)	$R_{ extsf{ heta}JA}$	100	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage	BV _{DSS}	28	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_		800	nA	$V_{DS} = 28V, V_{GS} = 0V$	
Gate-Body Leakage	IGSS	_		±80 ±800	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 19V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V _{GS(th)}	0.62	0.92	1.4	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	60 90	85 115	mΩ	$V_{GS} = 4.5V, I_D = 3.6A$ $V_{GS} = 2.5V, I_D = 3.1A$	
Forward Transconductance	Y _{fs}		3		S	$V_{DS} = 5V, I_D = 3.1A$	
Source-Drain Diode Forward Voltage	V _{SD}	_		1.16	V	$V_{GS} = 0V, I_{S} = 2.0A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	Ciss	_	305		pF		
Output Capacitance	Coss	_	74		pF	V _{DS} = 5V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	48	_	pF		

1. Device mounted on FR-4 PCB. t \leq 5 sec.

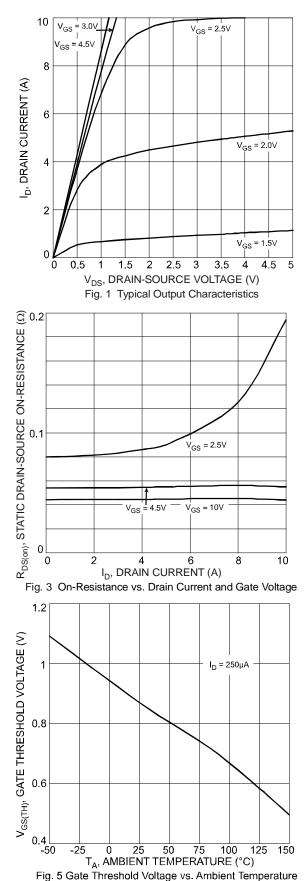
2. No purposefully added lead.

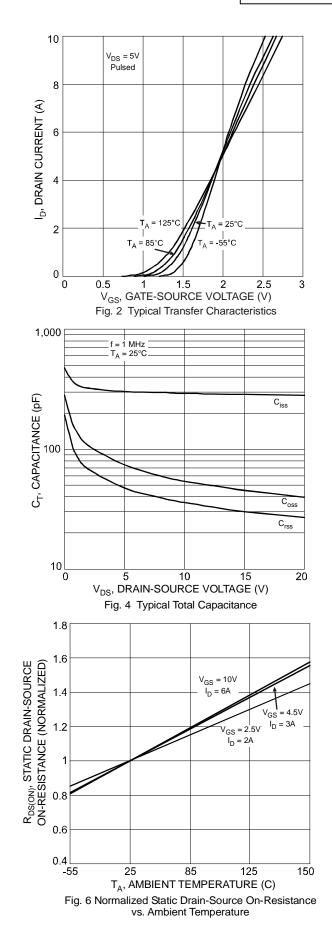
3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

4. Short duration pulse test used to minimize self-heating effect.

Notes:

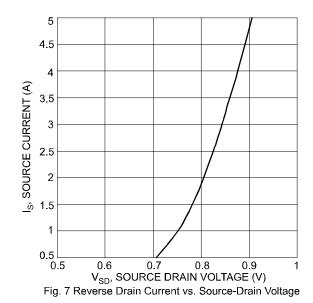






NEW PRODUCT



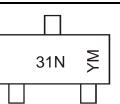


Ordering Information (Note 5)

Part Number	Case	Packaging
DMN3150L-7	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

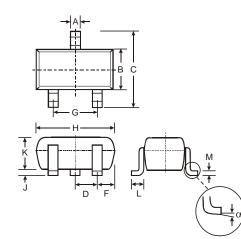


31N = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	2000	ô	2007		2008	20	09	2010		2011	2	2012
Code	Т		U		V	V	V	Х		Y		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

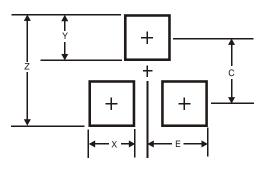
Package Outline Dimensions



SOT-23				
Dim	Min	Max		
Α	0.37	0.51		
В	1.20	1.40		
С	2.30	2.50		
D	0.89	1.03		
F	0.45	0.60		
G	1.78	2.05		
Н	2.80	3.00		
J	0.013	0.10		
K	0.903	1.10		
L	0.45	0.61		
М	0.085	0.180		
α	0°	8°		



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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